

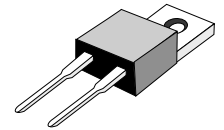
### High Efficiency Recovery Rectifier Diodes

... Designed for use in switching power supplies, inverters and as free wheeling diodes. These state-of-the-art devices have the following features:

- \* High Surge Capacity
- \* Low Power Loss, High efficiency
- \* Glass Passivated chip junctions
- \* 150 °C Operating Junction Temperature
- \* Low Stored Charge Majority Carrier Conduction
- \* Low Forward Voltage , High Current Capability
- \* High-Switching Speed 50 Nanosecond Recovery Time
- \* Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O

**HIGH EFFICIENCY  
RECTIFIERS**

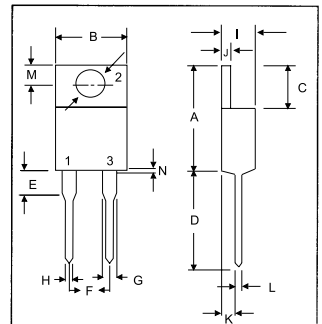
**8 AMPERES  
50 -- 200 VOLTS**



**TO-220A**

#### MAXIMUM RATINGS

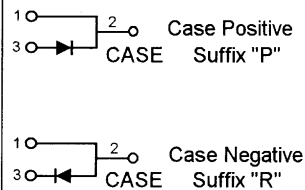
Characteristic	Symbol	H08A				Unit
		05	10	15	20	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	50	100	150	200	V
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	105	140	V
Average Rectifier Forward Current	$I_{F(AV)}$	8.0				A
Non-Repetitive Peak Surge Current ( Surge applied at rate load conditions halfwave, single phase, 60Hz )	$I_{FSM}$	150				A
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	- 65 to + 150				°C



DIM	MILLIMETERS	
	MIN	MAX
A	14.68	15.32
B	9.78	10.42
C	6.01	6.52
D	13.06	14.62
E	3.57	4.07
F	4.83	5.33
G	1.12	1.36
H	0.72	0.96
I	4.22	4.98
J	1.14	1.36
K	2.20	2.97
L	0.33	0.55
M	2.48	2.98
N	--	1.00
O	3.70	3.90

#### ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	H08A				Unit
		05	10	15	20	
Maximum Instantaneous Forward Voltage ( $I_F=8.0$ Amp, $T_C=25$ °C) ( $I_F=8.0$ Amp, $T_C=100$ °C)	$V_F$	1.00 0.88				V
Maximum Instantaneous Reverse Current ( Rated DC Voltage, $T_C=25$ °C) ( Rated DC Voltage, $T_C=100$ °C)	$I_R$	10 500				uA
Reverse Recovery Time ( $I_F=0.5$ A, $I_R=1.0$ A , $I_{rr}=0.25$ A )	$T_{rr}$	50				ns
Typical Junction Capacitance ( Reverse Voltage of 4 volts & f=1 MHz)	$C_P$	120				pF



# H08A05 Thru H08A20

FIG-1 TYPICAL FORWARD CHARACTERISTICS

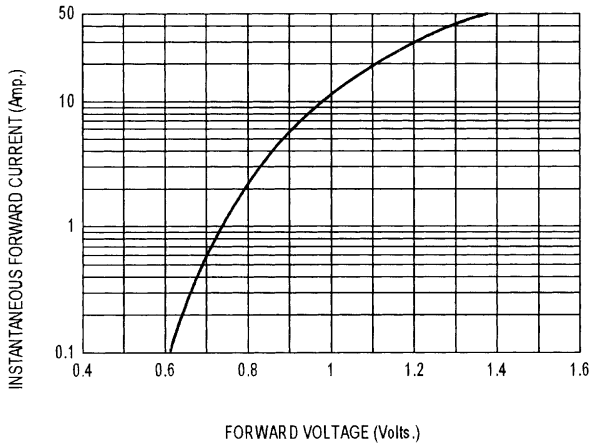


FIG-2 TYPICAL REVERSE CHARACTERISTICS

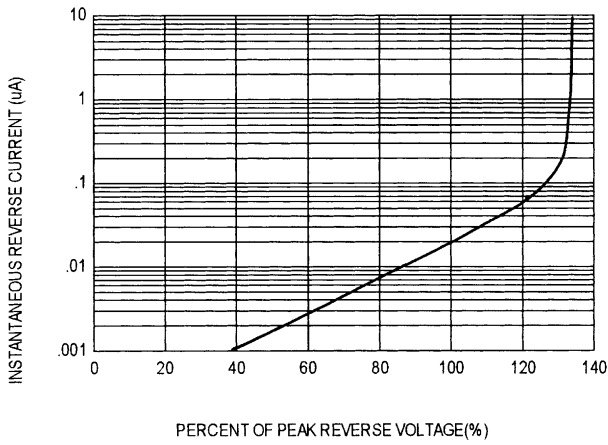


FIG-3 FORWARD CURRENT DERATING CURVE

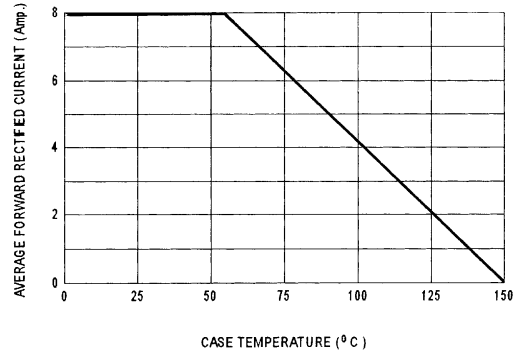


FIG-4 TYPICAL JUNCTION CAPACITANCE

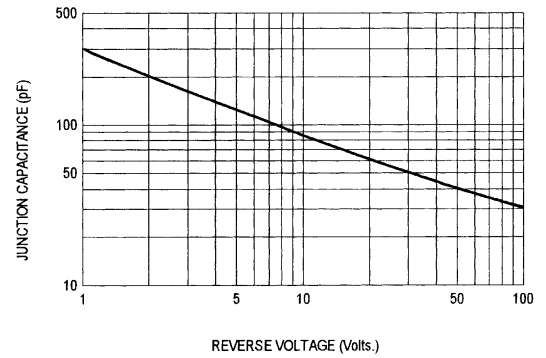
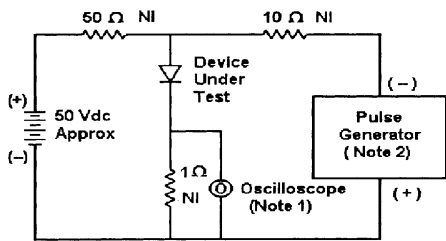
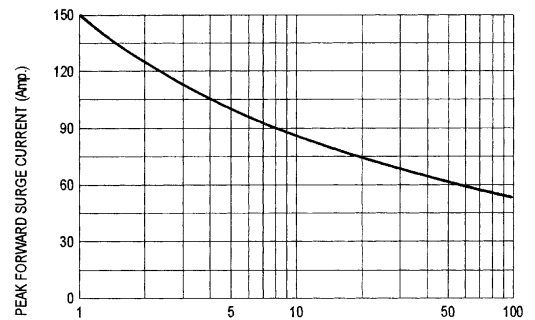
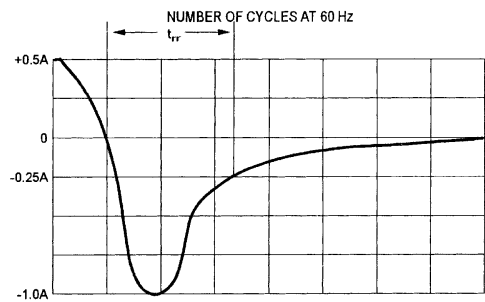


FIG-5 PEAK FORWARD SURGE CURRENT



Notes:  
 1. Rise Time = 7 ns max. Input Impedance = 1 M Ω , 22 pF  
 2. Rise Time = 10 ns max. Input Impedance = 50 Ω



Set time base for 20 ns/div

Fig-6 Reverse Recovery Time Characteristic and Test Circuit Diagram

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